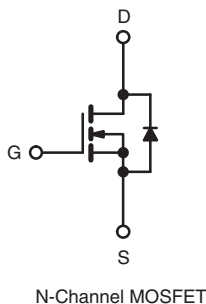
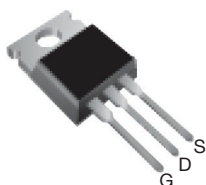


Power MOSFET

PRODUCT SUMMARY

| | | |
|---------------------------|------------------|------|
| V_{DS} (V) | 100 | |
| $R_{DS(on)}$ (Ω) | $V_{GS} = 5.0$ V | 0.27 |
| Q_g (Max.) (nC) | 12 | |
| Q_{gs} (nC) | 3.0 | |
| Q_{gd} (nC) | 7.1 | |
| Configuration | Single | |

TO-220AB


FEATURES

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Logic-Level Gate Drive
- $R_{DS(on)}$ Specified at $V_{GS} = 4$ V and 5 V
- 175 °C Operating Temperature
- Fast Switching
- Ease of Paralleling
- Compliant to RoHS Directive 2002/95/EC


RoHS*
COMPLIANT

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost the TO-220AB contribute to its wide acceptance throughout the industry.

ORDERING INFORMATION

| | |
|----------------|-------------------------|
| Package | TO-220AB |
| Lead (Pb)-free | IRL520PbF SiHL520-E3 |
| SnPb | IRL520 SiHL520 |

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

| PARAMETER | SYMBOL | LIMIT | UNIT |
|--|------------------|------------------|----------|
| Drain-Source Voltage | V_{DS} | 100 | V |
| Gate-Source Voltage | V_{GS} | ± 10 | |
| Continuous Drain Current | I_D | $T_C = 25$ °C | A |
| | | $T_C = 100$ °C | |
| Pulsed Drain Current ^a | I_{DM} | 36 | |
| Linear Derating Factor | | 0.40 | W/°C |
| Single Pulse Avalanche Energy ^b | E_{AS} | 170 | mJ |
| Avalanche Current ^a | I_{AR} | 9.2 | A |
| Repetitive Avalanche Energy ^a | E_{AR} | 6.0 | mJ |
| Maximum Power Dissipation | P_D | 60 | W |
| Peak Diode Recovery dV/dt^c | dV/dt | 5.5 | V/ns |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to + 175 | °C |
| Soldering Recommendations (Peak Temperature) | for 10 s | 300 ^d | |
| Mounting Torque | 6-32 or M3 screw | 10 | lbf · in |
| | | 1.1 | N · m |

Notes

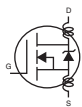

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 25$ V, starting $T_J = 25$ °C, $L = 3.0$ mH, $R_g = 25$ Ω , $I_{AS} = 9.2$ A (see fig. 12).
- $I_{SD} \leq 9.2$ A, $dI/dt \leq 110$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 175$ °C.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS

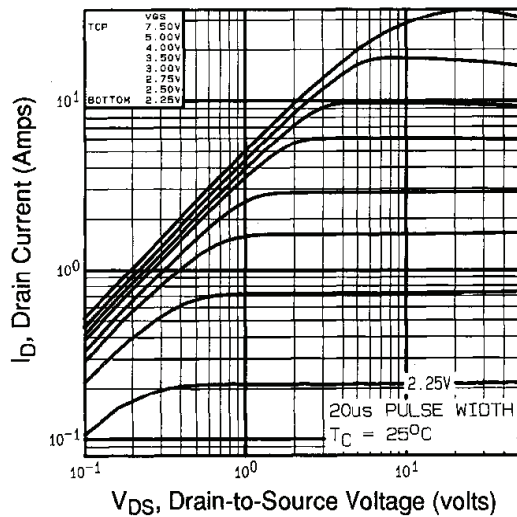
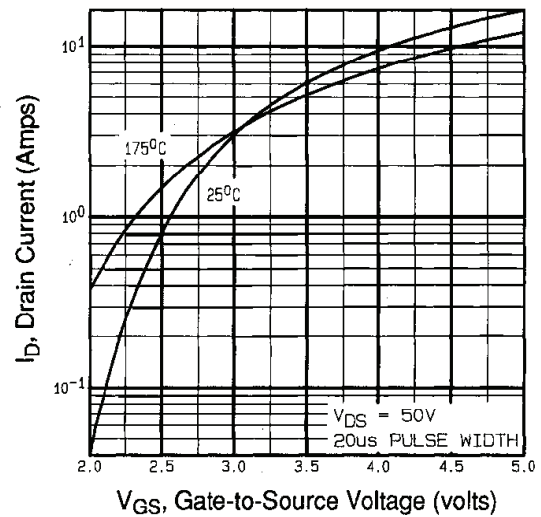
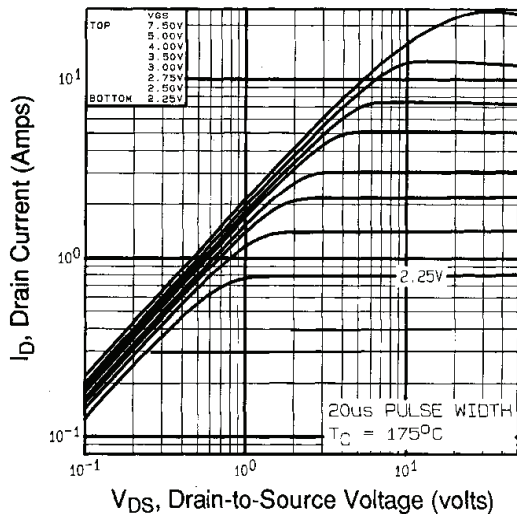
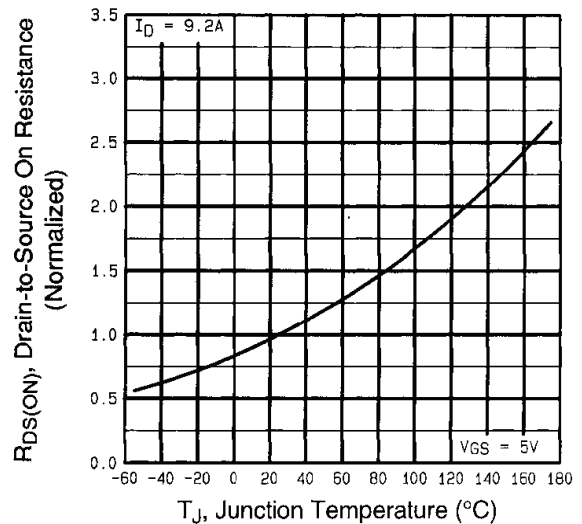
| PARAMETER | SYMBOL | TYP. | MAX. | UNIT |
|------------------------------------|------------|------|------|------|
| Maximum Junction-to-Ambient | R_{thJA} | - | 62 | °C/W |
| Case-to-Sink, Flat, Greasd Surface | R_{thCS} | 0.50 | - | |
| Maximum Junction-to-Case (Drain) | R_{thJC} | - | 2.5 | |

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
|---|----------------------------------|--|---|------|------|-------|------|
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V _{DS} | V _{GS} = 0 V, I _D = 250 μA | | 100 | - | - | V |
| V _{DS} Temperature Coefficient | ΔV _{DS} /T _J | Reference to 25 °C, I _D = 1 mA | | - | 0.12 | - | V/°C |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = 250 μA | | 1.0 | - | 2.0 | V |
| Gate-Source Leakage | I _{GSS} | V _{GS} = ± 10 V | | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 100 V, V _{GS} = 0 V | | - | - | 25 | μA |
| | | V _{DS} = 80 V, V _{GS} = 0 V, T _J = 150 °C | | - | - | 250 | |
| Drain-Source On-State Resistance | R _{DS(on)} | V _{GS} = 5.0 V | I _D = 5.5 A ^b | - | - | 0.27 | Ω |
| | | V _{GS} = 4.0 V | I _D = 4.6 A ^b | - | - | 0.38 | |
| Forward Transconductance | g _{fs} | V _{DS} = 50 V, I _D = 5.5 A | | 3.2 | - | - | S |
| Dynamic | | | | | | | |
| Input Capacitance | C _{iss} | V _{GS} = 0 V, V _{DS} = 25 V, f = 1.0 MHz, see fig. 5 | | - | 490 | - | pF |
| Output Capacitance | C _{oss} | | | - | 150 | - | |
| Reverse Transfer Capacitance | C _{rss} | | | - | 30 | - | |
| Total Gate Charge | Q _g | V _{GS} = 5.0 V | I _D = 9.2 A, V _{DS} = 80 V, see fig. 6 and 13 ^b | - | - | 12 | nC |
| Gate-Source Charge | Q _{gs} | | | - | - | 3.0 | |
| Gate-Drain Charge | Q _{gd} | | | - | - | 7.1 | |
| Turn-On Delay Time | t _{d(on)} | V _{DD} = 50 V, I _D = 9.2 A, R _g = 9.0 Ω, R _D = 5.2 Ω, see fig. 10 ^b | | - | 9.8 | - | ns |
| Rise Time | t _r | | | - | 64 | - | |
| Turn-Off Delay Time | t _{d(off)} | | | - | 21 | - | |
| Fall Time | t _f | | | - | 27 | - | |
| Internal Drain Inductance | L _D | Between lead, 6 mm (0.25") from package and center of die contact  | | - | 4.5 | - | nH |
| Internal Source Inductance | L _S | | | - | 7.5 | - | |
| Drain-Source Body Diode Characteristics | | | | | | | |
| Continuous Source-Drain Diode Current | I _S | MOSFET symbol showing the integral reverse p - n junction diode  | | - | - | 9.2 | A |
| Pulsed Diode Forward Current ^a | I _{SM} | | | - | - | 36 | |
| Body Diode Voltage | V _{SD} | T _J = 25 °C, I _S = 9.2 A, V _{GS} = 0 V ^b | | - | - | 2.5 | V |
| Body Diode Reverse Recovery Time | t _{rr} | T _J = 25 °C, I _F = 9.2 A, dI/dt = 100 A/μs ^b | | - | 130 | 190 | ns |
| Body Diode Reverse Recovery Charge | Q _{rr} | | | - | 0.83 | 1.0 | μC |
| Forward Turn-On Time | t _{on} | Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D) | | | | | |

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\text{ }\%$.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^{\circ}\text{C}$

Fig. 3 - Typical Transfer Characteristics

Fig. 2 - Typical Output Characteristics, $T_C = 175\text{ }^{\circ}\text{C}$

Fig. 4 - Normalized On-Resistance vs. Temperature

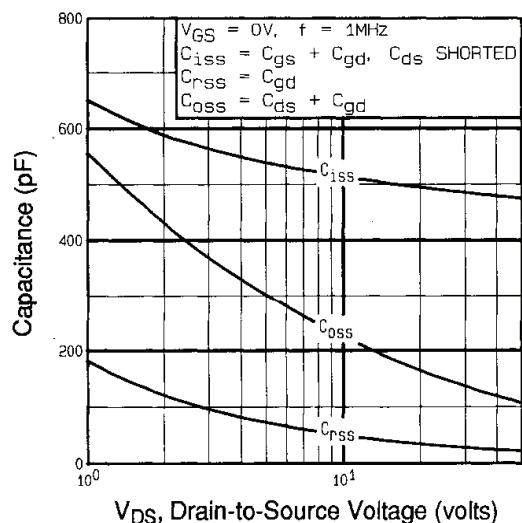


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

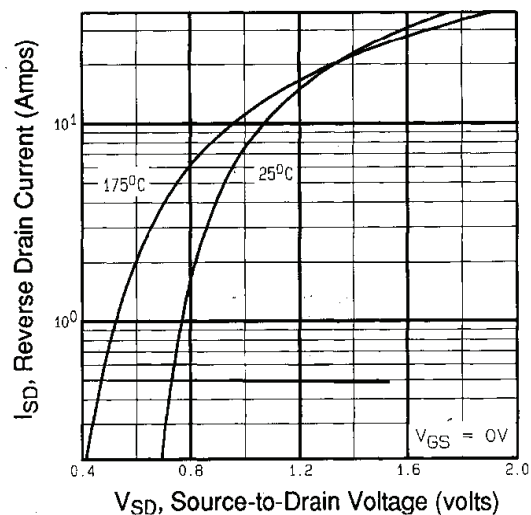


Fig. 7 - Typical Source-Drain Diode Forward Voltage

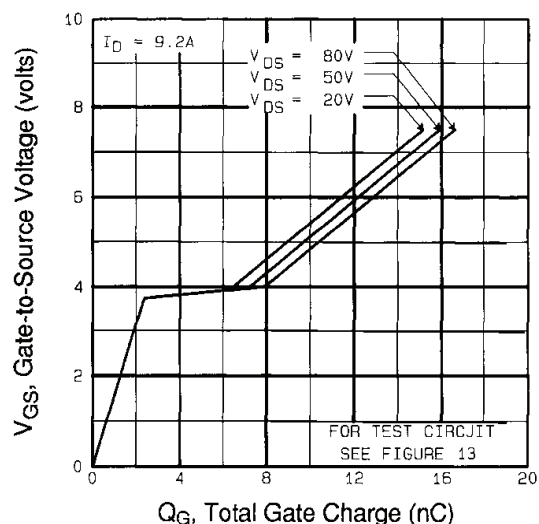


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

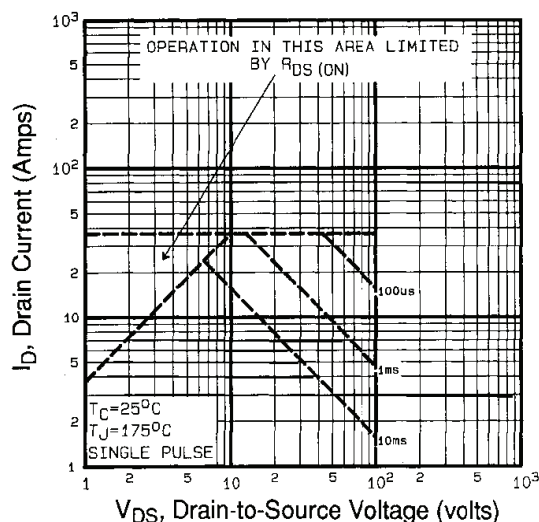
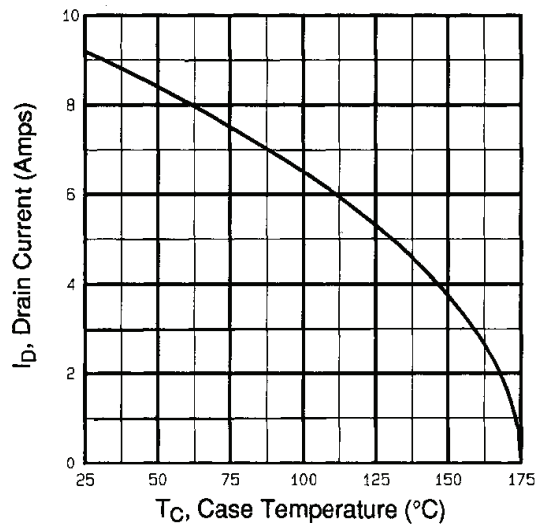
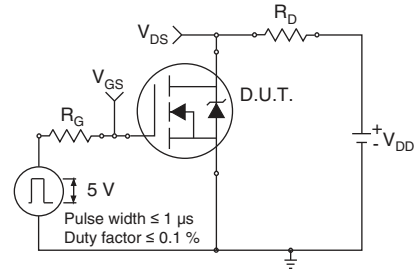
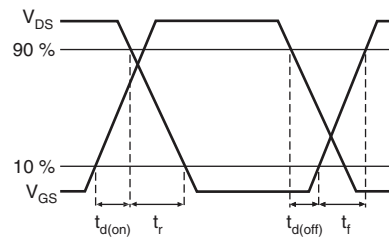
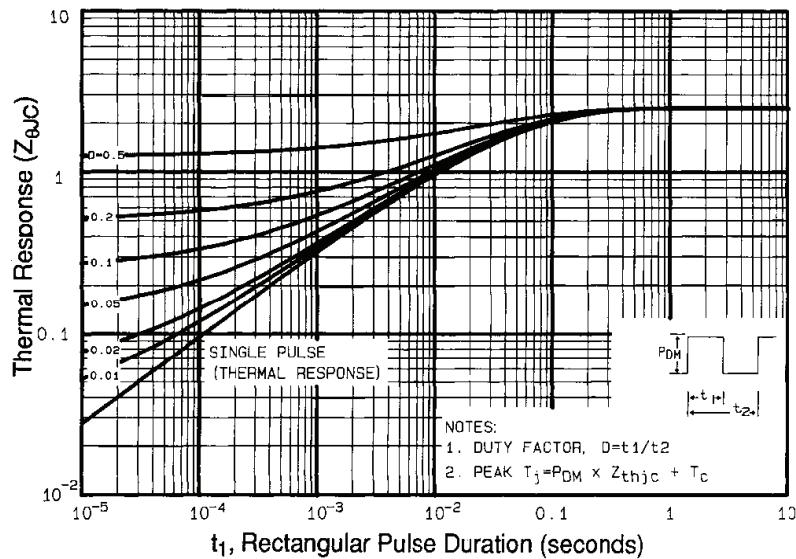


Fig. 8 - Maximum Safe Operating Area


Fig. 9 - Maximum Safe Operating Area

Fig. 10a - Switching Time Test Circuit

Fig. 10b - Switching Time Waveforms

Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

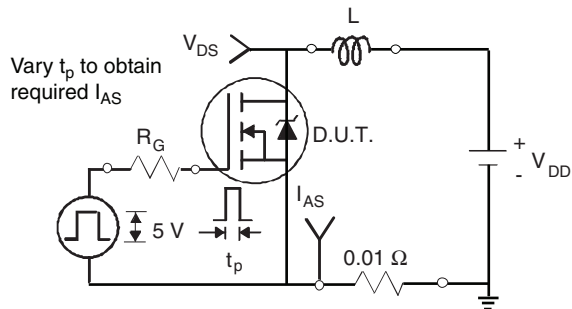


Fig. 12a - Unclamped Inductive Test Circuit

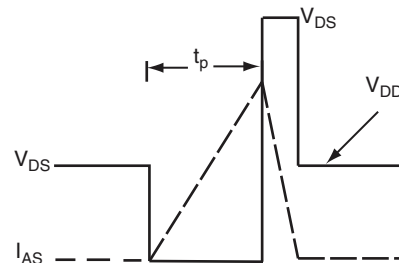


Fig. 12b - Unclamped Inductive Waveforms

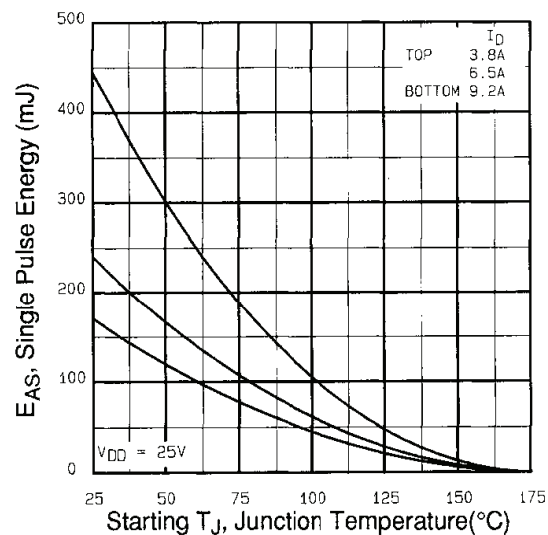


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

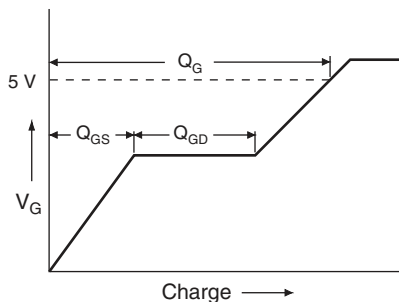


Fig. 13a - Basic Gate Charge Waveform

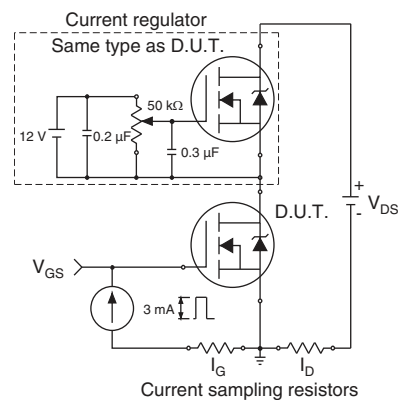
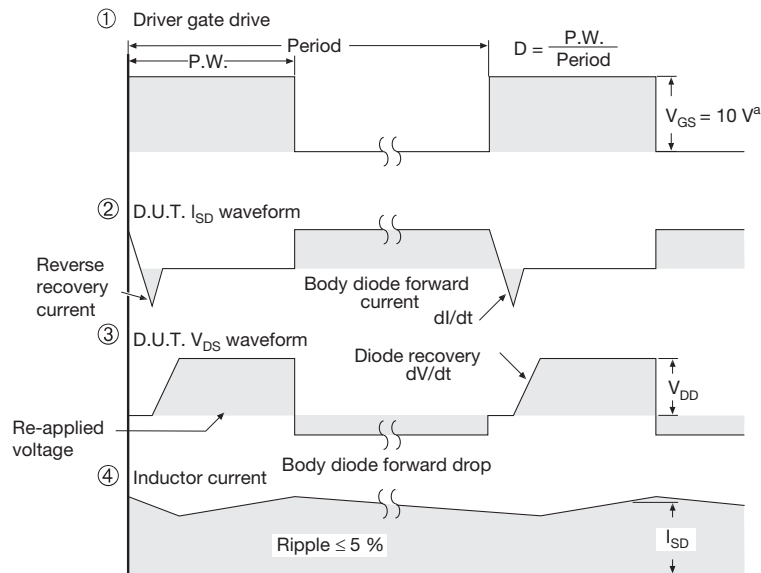
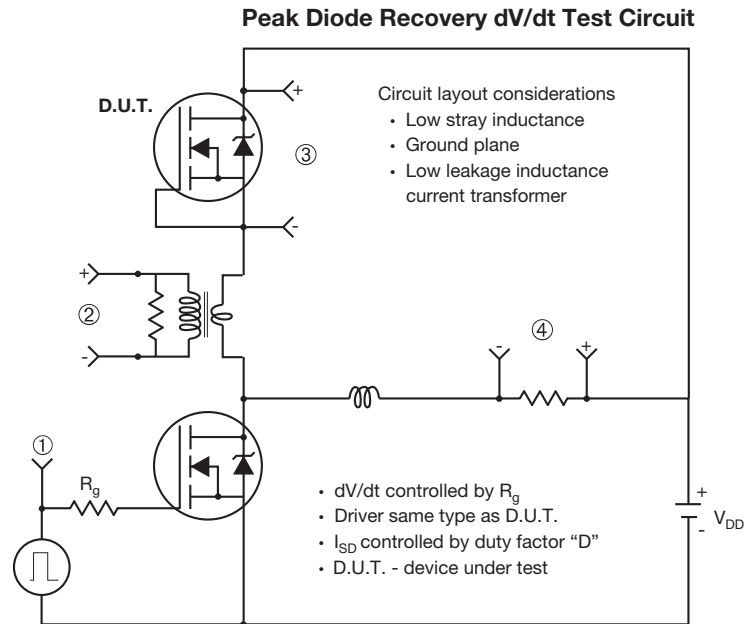
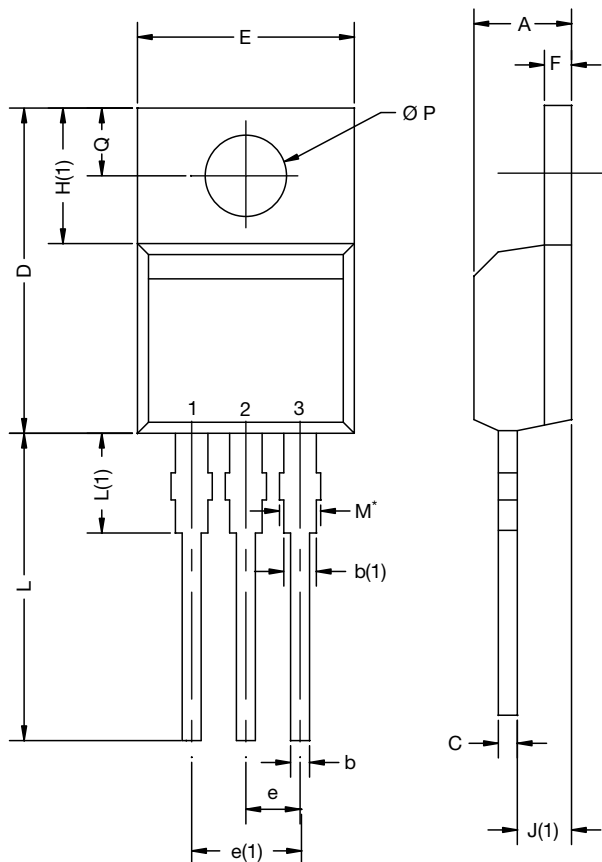


Fig. 13b - Gate Charge Test Circuit


Fig. 14 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91298.

TO-220-1

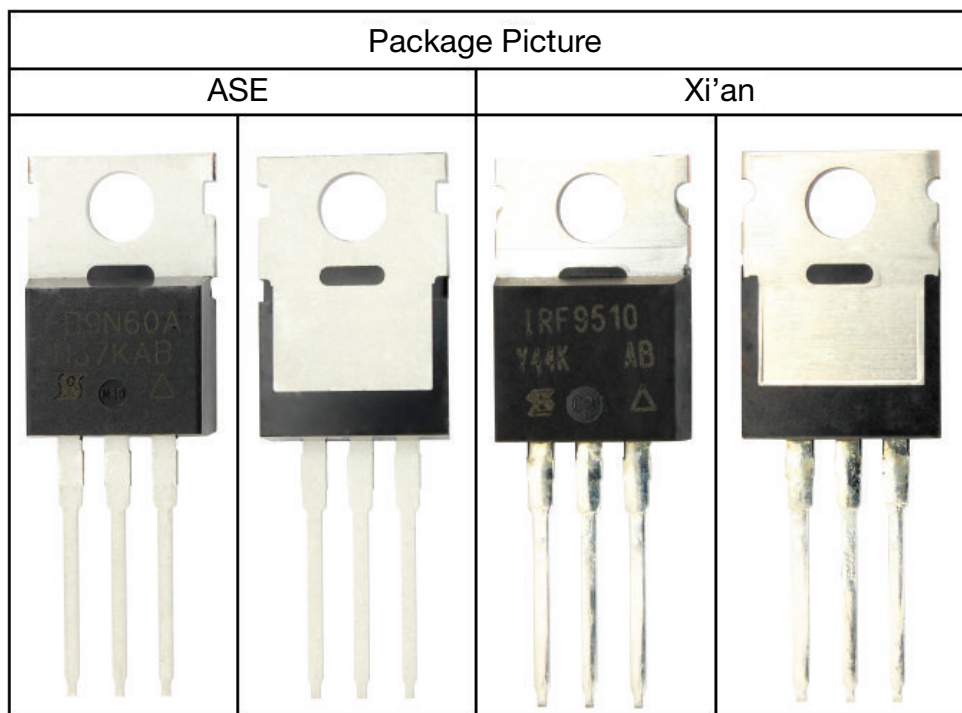


| DIM. | MILLIMETERS | | INCHES | |
|------|-------------|-------|--------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 4.24 | 4.65 | 0.167 | 0.183 |
| b | 0.69 | 1.02 | 0.027 | 0.040 |
| b(1) | 1.14 | 1.78 | 0.045 | 0.070 |
| c | 0.36 | 0.61 | 0.014 | 0.024 |
| D | 14.33 | 15.85 | 0.564 | 0.624 |
| E | 9.96 | 10.52 | 0.392 | 0.414 |
| e | 2.41 | 2.67 | 0.095 | 0.105 |
| e(1) | 4.88 | 5.28 | 0.192 | 0.208 |
| F | 1.14 | 1.40 | 0.045 | 0.055 |
| H(1) | 6.10 | 6.71 | 0.240 | 0.264 |
| J(1) | 2.41 | 2.92 | 0.095 | 0.115 |
| L | 13.36 | 14.40 | 0.526 | 0.567 |
| L(1) | 3.33 | 4.04 | 0.131 | 0.159 |
| Ø P | 3.53 | 3.94 | 0.139 | 0.155 |
| Q | 2.54 | 3.00 | 0.100 | 0.118 |

ECN: X15-0364-Rev. C, 14-Dec-15
DWG: 6031

Note

- M* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM





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